



PATENT  
Attorney Docket No.: SAM-0274

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Min-su Kim, et al.

Serial No.: 09/994,146

Filing Date: November 26, 2001

Title: SEMICONDUCTOR DEVICE HAVING SILICON-ON-INSULATOR  
STRUCTURE AND METHOD OF FABRICATING THE SAME

Examiner: Hu, S.

Group Art Unit: 2811

8/B  
1.84702  
9-27

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Post Office as First Class Mail on the date indicated below in an envelope addressed to BOX NON-FEE AMENDMENT, Assistant Commissioner for Patents, Washington, DC 20231.

9/16/02  
Date

Lisa Sanders  
Lisa Sanders

BOX NON-FEE AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

AMENDMENT A

Sir:

This is in response to the Office Action mailed on June 17, 2002.

Please amend the application as follows:

In the Claims

- Sub D27  
B1  
cont.
1. (Amended) A semiconductor device having a silicon-on-insulator (SOI) structure, comprising:
    - an insulating layer;
    - an insular silicon region having first conductive impurity ions formed on the insulating layer;
    - a source region having second conductive impurity ions formed at an end of the insular silicon region;

RECEIVED  
SEP 25 2002  
TECHNOLOGY CENTER 2800